

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07354 DT-33-21

2SB754

SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

Unit in mm

HIGH CURRENT SWITCHING APPLICATIONS.

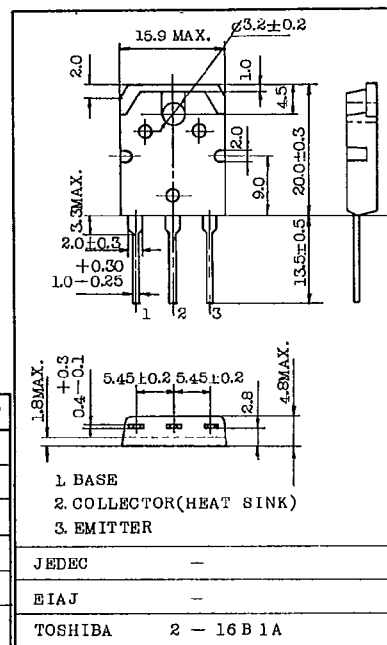
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- High Collector Current : $I_C = -7A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.4V$ (Max.) at $I_C = -4A$
- High Power Dissipation : $P_C = 60W$ at $T_c = 25^\circ C$
- Complementary to 2SD844.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-7	A
Emitter Current	I_E	7	A
Collector Power Dissipation	P_C	$T_a = 25^\circ C$	2.5
		$T_c = 25^\circ C$	60
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Weight : 4.6g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$	-	-	-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-10	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10mA, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1V, I_C = -1A$	70	-	240	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -4A$	30	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -4A, I_B = -0.4A$	-	-0.2	-0.4	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1V, I_C = -4A$	-	-0.9	-1.2	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -1A$	-	10	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	300	-	pF

Note : $h_{FE(1)}$ Classification O : 70~140 Y : 120~240

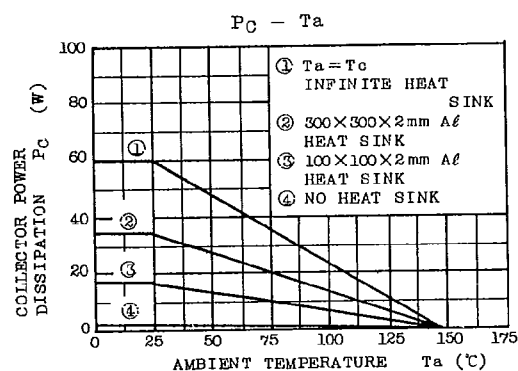
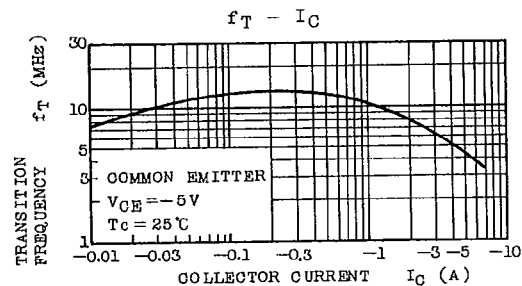
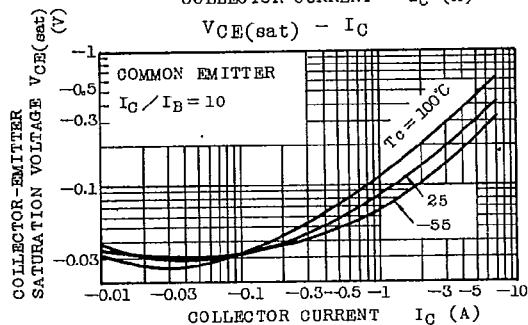
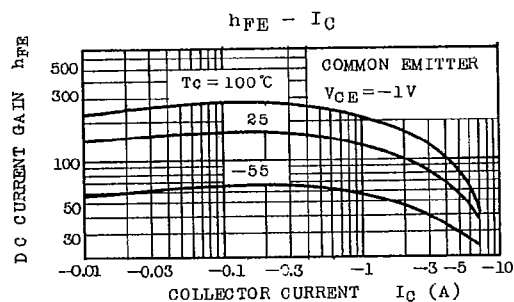
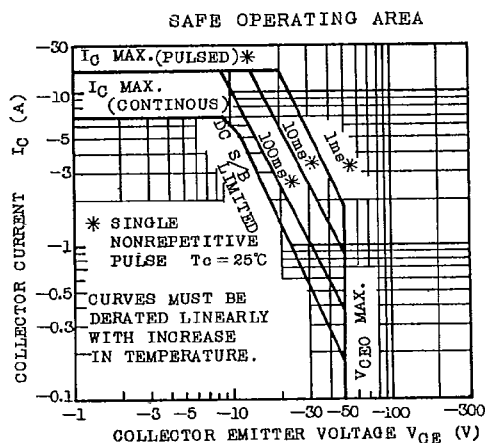
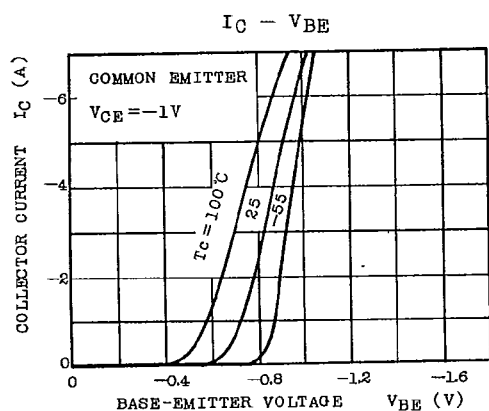
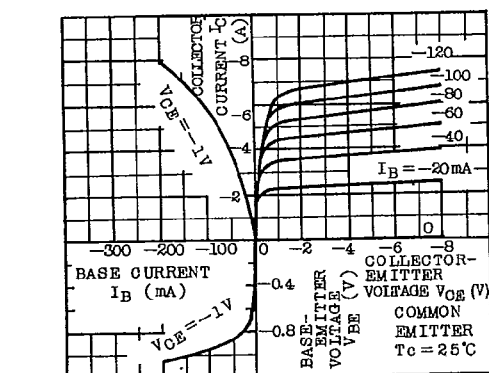
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STATIC CHARACTERISTICS



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